# **CEL** California Eastern Laboratories

**Evaluation Board Document** 

# NE5550234-EV09-A

# **Evaluation Board**

- Circuit Description
- Typical Performance Data
- Circuit Schematic and Assembly Drawing

## **Circuit Description**

The NE5550234-EV09-A is an evaluation circuit board for Renesas' LDMOS power FET, NE5550234 optimized for the performance at 915MHz. The circuit board is RoHS compliant.

#### **Matching and Bias Circuits**

Refer to the schematic and assembly drawing in the two last pages for the component designation and location.

The input matching circuit consists of two sections of low pass network. An inductor, L1 and a section of transmission line, TL4 are the serial components in the network. At output, three sections of transmission line, TL1, TL2 and TL3 provide the required serial components for the impedance transformation. The performance is most sensitive to the length of TL1 and not very sensitive to TL3. The electrical lengths of the transmission lines labeled on the schematic are estimated and for reference only. Some bench tuning on the actual circuit board is usually required to achieve an optimal performance. For applications where there is a constraint on the board space, serial inductors, instead of transmission lines, can be used for the matching circuits. Low loss inductors should be selected to maintain good efficiency of the PA circuit. The resistor, R3(=2.40hm) at input is used to improve the stability margin. The gain is reduced by about 1-2dB when R3 is used.

LDMOSFETs essentially draw no gate current under normal operation conditions. Therefore a large value resistor, in the order of  $k\Omega$ , can be used for the bias at gate so that the RF path is completely isolated from the DC line. At the drain an inductor is used as the RF choke. The current rating for this inductor should be high enough to provide the required current at the operation conditions.

#### **Bias Conditions**

This evaluation board was optimized at a specific drain voltage, 7.5V. For different supply voltages, the matching circuits should be adjusted to fully utilize the device capability. The quiescent current is 40mA for the data shown below. The gain is higher at higher quiescent currents, particularly when the device is not completely saturated. For many communication systems, where the PA is never at idle state, a high quiescent current might be used.

#### **PCB Material:**

The PCB is Getek 28mil two layer board. The dielectric constant of Getek is 4.2.

## Typical Performance Data

Test Conditions:

f=915MHz

Vd=7.5V, Idsq=40mA

Pout, Gain, PAE and Current vs Pin are shown in the following plot.







### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Other Development Tools category:

Click to view products by CEL manufacturer:

Other Similar products are found below :

DS100BR410EVK-4/NOPB BK0004 BK0012 SN65MLVD2-3EVM DS80EP100-EVK MAX9684EVKIT# MAX4952AEVKIT+ ESD-EVM-001 MAX14842EVKIT+ EVAL01-HMC749LC3C 410-320 TPD6F002-Q1EVM TS9002DB DS80PCI800EVK/NOPB 118777-HMC722LC3C 118777-HMC723LC3C 118777-HMC678LC3C DC1765A-A 125614-HMC851LC3C DC2178A-A TPD1E05U06DPYEVM SN65LVDM31-32BEVM DC2062A-A NB4N855SMEVB LMH6321MR-EVAL/NOPB EVAL01-HMC747LC3C 4537 DK-M3F-1.8-TRK-1.5-S DK-M3-FS-1.8-1.5-M12/16 DK-M3-LS-1.8-6 ADALM1000 ADALP2000 EVAL-CN0202-SDPZ EVAL-CN0203-SDPZ EVAL-CN0204-SDPZ EVAL-CN0209-SDPZ EVAL-CN0225-SDPZ EVAL-CN0229-SDPZ EVAL-CN0251-SDPZ EVAL-CN0272-SDPZ EVAL-CN0301-SDPZ EVAL-CN0325-SDPZ EVAL-CN0355-PMDZ EVAL-CN0364-SDPZ EVAL-SDP-CB1Z DS1964SEVKIT# MAX14611EVKIT# MAX22088EVKIT# MAX4951AEEVKIT+ MAXREFDES60#